

# GD54/74HC30, GD54/74HCT30

## 8-INPUT NAND GATE

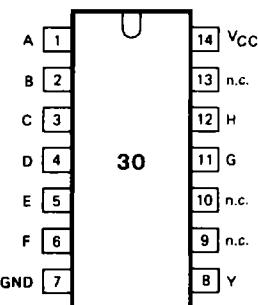
### General Description

These devices are identical in pinout to the 54/74LS30. They contain a single 8-input NAND gate. These devices are characterized for operation over wide temperature ranges to meet industry and military specifications.

### Features

- Low Power consumption characteristic of CMOS devices
- Output drive capability: 10 LS TTL Loads Min.
- Operating speed superior to LS TTL
- Wide operating voltage range: for HC 2 to 6 volts for HCT 4.5 to 5.5 volts
- Low input current: 1 $\mu$ A Max.
- Low quiescent current: 20 $\mu$ A Max. (74HC)
- High noise immunity characteristic of CMOS
- Diode protection on all inputs

### Pin Configuration



Suffix-Blank Plastic Dual In Line Package  
 Suffix-J Ceramic Dual In Line Package  
 Suffix-D Small Outline Package

### Logic Symbol and Diagram

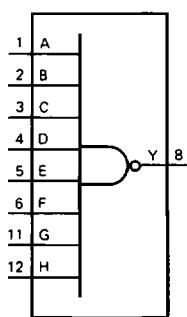


Fig. 1 Logic symbol

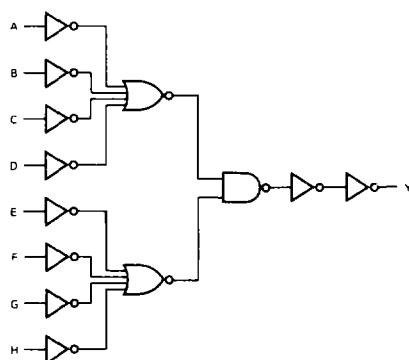


Fig. 2 Logic diagram

### Function Table

INPUTS									OUTPUT
A	B	C	D	E	F	G	H	Y	
L	X	X	X	X	X	X	X	H	
X	L	X	X	X	X	X	X	H	
X	X	L	X	X	X	X	X	H	
X	X	X	L	X	X	X	X	H	
X	X	X	X	L	X	X	X	H	
X	X	X	X	X	L	X	X	H	
X	X	X	X	X	X	L	X	H	
X	X	X	X	X	X	X	L	H	
H	H	H	H	H	H	H	H	L	

H=HIGH voltage level

L=LOW voltage level

X=don't care

# GD54/74HC30, GD54/74HCT30

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## Absolute Maximum Ratings

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CC}$	DC Supply voltage		-0.5	+7	V
$I_{IK}, I_{OK}$	DC input or output diode current	for $V_I < -0.5$ or $V_I > V_{CC} + 0.5V$		20	mA
$I_O$	DC output source or sink current	for $-0.5V < V_O < V_{CC} + 0.5V$		25	mA
$I_{CC}$	DC $V_{CC}$ or GND current			50	mA
$T_{STG}$	Storage temperature range		-65	150	°C
$P_D$	Power dissipation per package	above $+70^{\circ}\text{C}$ derate linearly with $8\text{mW/K}$		500	mW
$T_L$	Lead temperature	At distance $1/16 \pm 1/32$ in from case for 60 sec(CERAMIC) 10 sec(PLASTIC)		300 260	°C

## Recommended Operating Conditions

CHARACTERISTIC	LIMITS		UNITS
	MIN.	MAX.	
Supply-Voltage Range $V_{CC}$ : GD54/74HC Types GD54/74HCT Types	2 4.5	6 5.5	V
DC Input or Output Voltage $V_I, V_O$	0	$V_{CC}$	V
Operating Temperature $T_A$ : GD74 Types GD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall times $t_r, t_f$ : GD54/74HC Types at 2V at 4.5V at 6V GD54/74HCT Types at 4.5V		1000 500 400 500	ns

**DC Electrical Characteristics for HC**

SYMBOL	PARAMETER	TEST CONDITION	V <sub>CC</sub> (V)	T <sub>A</sub> =25°C			GD74HC30		GD54HC30		UNIT
				MIN	TYP.	MAX	MIN.	MAX.	MIN	MAX	
V <sub>IH</sub>	HIGH level input Voltage		2.0 4.5 6.0	1.5 3.15 4.2			1.5 3.15 4.2		1.5 3.15 4.2		V
V <sub>IL</sub>	LOW level input voltage		2.0 4.5 6.0			0.3 0.9 1.2		0.3 0.9 1.2		0.3 0.9 1.2	V
V <sub>OH</sub>	HIGH level output voltage	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> =-20μA	2.0 4.5 6.0	1.9 4.4 5.9	2.0 4.5 6.0	1.9 4.4 5.9		1.9 4.4 5.9		V
			I <sub>OH</sub> =-4mA I <sub>OH</sub> =-5.2mA	4.5 6.0	3.98 5.48	4.3 5.2		3.84 5.34		3.7 5.2	
V <sub>OL</sub>	LOW level output voltage	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> =20μA	2.0 4.5 6.0		0.1 0.1 0.1		0.1 0.1 0.1		0.1 0.1 0.1	V
			I <sub>OL</sub> =4mA I <sub>OL</sub> =5.2mA	4.5 6.0		0.17 0.15	0.26 0.26		0.33 0.33		0.4 0.4
I <sub>IN</sub>	Input leakage Current	V <sub>IN</sub> =V <sub>CC</sub> or GND	6.0			0.1		1.0		1.0	μA
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>out</sub> =0μA	6.0			2		20		40	μA

**DC Electrical Characteristics for HCT**

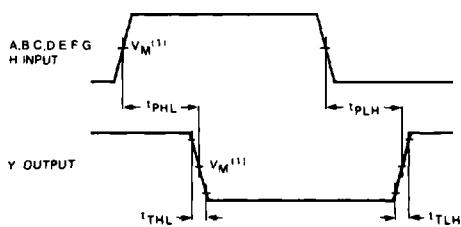
SYMBOL	PARAMETER	TEST CONDITION	V <sub>CC</sub> (V)	T <sub>A</sub> =25°C			GD74HCT30		GD54HCT30		UNIT
				MIN	TYP.	MAX	MIN	MAX	MIN	MAX	
V <sub>IH</sub>	HIGH level input Voltage		4.5 to 5.5	2.0			2.0		2.0		V
V <sub>IL</sub>	LOW level input voltage		4.5 to 5.5			0.8		0.8		0.8	V
V <sub>OH</sub>	HIGH level output voltage	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OH</sub> =-20μA	4.5	4.4	4.5		4.4		4.4	V
			I <sub>OH</sub> =-4mA	4.5	3.98	4.3		3.84		3.7	
V <sub>OL</sub>	LOW level output voltage	V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub>	I <sub>OL</sub> =20μA	4.5		0.1		0.1		0.1	V
			I <sub>OL</sub> =4mA	4.5		0.17	0.26		0.33		0.4
I <sub>IN</sub>	Input leakage Current	V <sub>IN</sub> =V <sub>CC</sub> or GND	5.5			0.1		1.0		1.0	μA
I <sub>CC</sub>	Quiescent Supply Current	V <sub>IN</sub> =V <sub>CC</sub> or GND I <sub>out</sub> =0μA	5.5			2		20		40	μA

**AC Characteristics for HC:  $t_r=t_f=6\text{ns}$   $C_L=50\text{pF}$** 

SYMBOL	PARAMETER	V <sub>CC</sub> (V)	T <sub>A</sub> =25°C			GD74HC30		GD54HC30		UNIT
			MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.	
$t_{PLH}/t_{PHL}$	Propagation delay time A, B, C, D, E, F, G, H to Y	2.0		35	110		150		180	ns
		4.5		12	24		30		36	
		6.0		10	20		26		32	
$t_{TLH}/t_{THL}$	Output transition time	2.0		25	70		85		100	ns
		4.5		8	15		18		22	
		6.0		7	13		16		19	

**AC Characteristics for HCT:  $t_r=t_f=6\text{ns}$   $C_L=50\text{pF}$** 

SYMBOL	PARAMETER	V <sub>CC</sub> (V)	T <sub>A</sub> =25°C			GD74HCT30		GD54HCT30		UNIT	
			MIN.	TYP.	MAX.	MIN.	MAX.	MIN.	MAX.		
$t_{PLH}/t_{PHL}$	Propagation delay time A, B, C, D, E, F, G, H to Y	4.5			15	28		36		ns	
									42		
$t_{TLH}/t_{THL}$	Output transition time	4.5			8	15		19		22	ns

**AC Waveform**

**Fig. 3** Waveforms showing the input (A,B,C,D,E,F,G,H) to output (Y) propagation delays and the output transition times.

**Note to AC waveform**

- (1) HC :  $V_M=50\%$ ,  $V_i=\text{GND}$  to  $V_{cc}$
- HCT :  $V_M=1.3V$ ,  $V_i=\text{GND}$  to  $3V$